# **Hex Inverter**

# With LSTTL-Compatible Inputs High-Performance Silicon-Gate CMOS

The MC74HCT04A may be used as a level converter for interfacing TTL or NMOS outputs to High-Speed CMOS inputs. The HCT04A is identical in pinout to the LS04.

### **Features**

- Output Drive Capability: 10 LSTTL Loads
- TTL/NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1µA
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 48 FETs or 12 Equivalent Gates
- Pb-Free Packages are Available



# ON Semiconductor®

http://onsemi.com

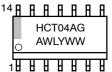
MARKING DIAGRAMS



PDIP-14 N SUFFIX CASE 646



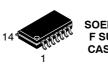
SOIC-14 D SUFFIX CASE 751A



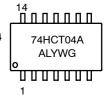


TSSOP-14 DT SUFFIX CASE 948G





SOEIAJ-14 F SUFFIX CASE 965



A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week

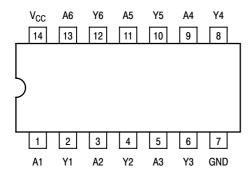
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

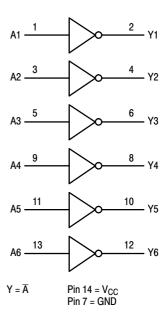
Pinout: 14-Lead Packages (Top View)



# **FUNCTION TABLE**

Inputs	Outputs
Α	Y
L	Н
Н	L

# LOGIC DIAGRAM



# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>	
MC74HCT04AN	PDIP-14		
MC74HCT04ANG	PDIP-14 (Pb-Free)	25 Units / Rail	
MC74HCT04AD	SOIC-14		
MC74HCT04ADG	SOIC-14 (Pb-Free)	55 Units / Rail	
MC74HCT04ADR2	SOIC-14		
MC74HCT04ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel	
MC74HCT04ADTR2	TSSOP-14*		
MC74HCT04ADTR2G	TSSOP-14*		
MC74HCT04AFEL	SOEIAJ-14		
MC74HCT04AFELG	SOEIAJ-14 (Pb-Free)	2000 / Tape & Reel	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>This package is inherently Pb-Free.

### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V
I <sub>in</sub>	DC Input Current, per Pin	±[ <b>2</b> 0	mA
l <sub>out</sub>	DC Output Current, per Pin	±[ <b>2</b> 5	mA
Icc	DC Supply Current, V <sub>CC</sub> and GND Pins	±[\$0	mA
P <sub>D</sub>	Power Dissipation in Still Air Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature Range	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range, All Package Types	<b>– 55</b>	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise/Fall Time (Figure 1)	0	500	ns

# DC CHARACTERISTICS (Voltages Referenced to GND)

			v <sub>cc</sub>	Guara	nteed Lin	nit	
Symbol	Parameter	Condition	v	-55 to 25°C	≤ <b>85</b> °C	≤125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = 0.1V$ $ I_{out}  \le 20\mu A$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$V_{out} = V_{CC} - 0.1V$ $ I_{out}  \le 20\mu A$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out}  \le 20\mu A$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IL}$ $ I_{out}  \le 4.0 \text{mA}$	4.5	3.98	3.84	3.70	
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out}  \le 20\mu A$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH}$ $ I_{out}  \le 4.0 \text{mA}$	4.5	0.26	0.33	0.40	
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5	±0.1	±1.0	±1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0\mu A$	5.5	1	10	40	μΑ
$\Delta I_{CC}$	Additional Quiescent Supply Current	V <sub>in</sub> = 2.4V, Any One Input		≥ -55°C	25 to	125°C	
	Ourent	$V_{in} = V_{CC}$ or GND, Other Inputs $I_{out} = 0\mu A$		2.9	2	.4	mA

<sup>1.</sup> Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

<sup>2.</sup> Total Supply Current =  $I_{CC} + \Sigma \Delta I_{CC}$ .

# AC CHARACTERISTICS ( $V_{CC}$ = 5.0V ±10%, $C_L$ = 50pF, Input $t_r$ = $t_f$ = 6ns)

		Guaranteed Limit			
Symbol	Parameter	-55 to 25°C	≤ <b>85°C</b>	≤125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 2)	15 17	19 21	22 26	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 2)	15	19	22	ns
C <sub>in</sub>	Maximum Input Capacitance	10	10	10	pF

<sup>3.</sup> For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Inverter)*	22	pF

<sup>\*</sup>Used to determine the no-load dynamic power consumption:  $P_D = C_{PD} \, V_{CC}^2 f + I_{CC} \, V_{CC}$ . For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

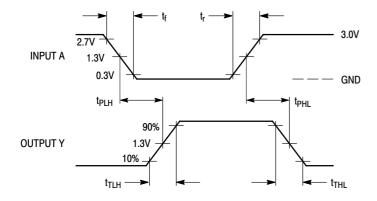
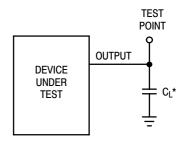


Figure 1. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 2. Test Circuit

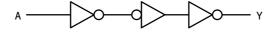
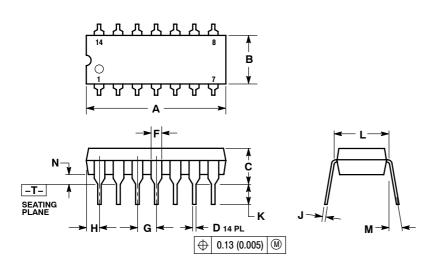


Figure 3. Expanded Logic Diagram (1/6 of the Device Shown)

# **PACKAGE DIMENSIONS**

PDIP-14 CASE 646-06 **ISSUE P** 

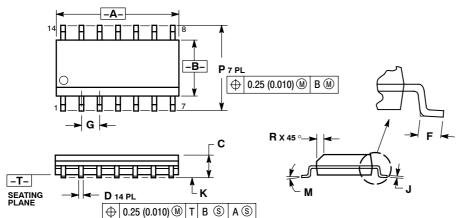


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
  5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54 BSC	
Н	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
М		10 °		10 °
N	0.015	0.039	0.38	1.01

### PACKAGE DIMENSIONS

SOIC-14 CASE 751A-03 **ISSUE H** 



### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

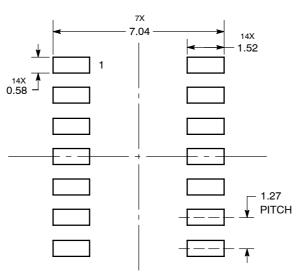
  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PER SIDE.
  5. DIMENSION D DOES NOT INCLUDE
  DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.127
  (0.005) TOTAL IN EXCESS OF THE D
  DIMENSION AT MAXIMUM MATERIAL
  CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	1.27 BSC		BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7°	0 °	7 °
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

### **SOLDERING FOOTPRINT\***

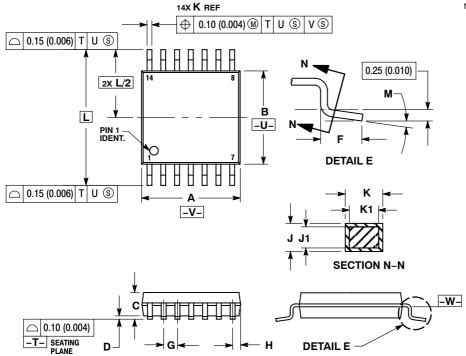


DIMENSIONS: MILLIMETERS

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### PACKAGE DIMENSIONS

## TSSOP-14 CASE 948G-01 **ISSUE B**

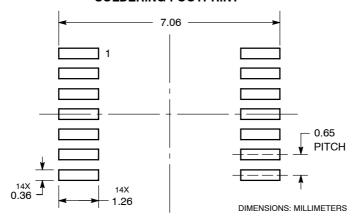


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: MILLIMETER.
   DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
   DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- NOT EXCEED 0.25 (0.010) PER SIDE.
  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

  7. DIMENSION A AND B ARE TO BE

DETE	<del>IRMINED AT DATUM PLANE -W</del>					
	MILLIN	IETERS	INC	HES		
DIM	MIN	MAX	MIN	MAX		
Α	4.90	5.10	0.193	0.200		
В	4.30	4.50	0.169	0.177		
С		1.20		0.047		
D	0.05	0.15	0.002	0.006		
F	0.50	0.75	0.020	0.030		
G	0.65	BSC	0.026	BSC		
Н	0.50	0.60	0.020	0.024		
J	0.09	0.20	0.004	0.008		
J1	0.09	0.16	0.004	0.006		
K	0.19	0.30	0.007	0.012		
K1	0.19	0.25	0.007	0.010		
L	6.40	BSC	0.252 BSC			
M	0 °	8 °	0 °	8 °		

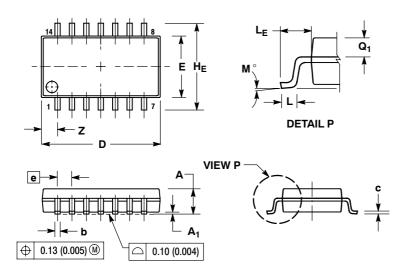
## **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### PACKAGE DIMENSIONS

SOEIAJ-14 CASE 965-01 ISSUE A



### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS D AND E DO NOT INCLUDE
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.80 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
$Q_1$	0.70	0.90	0.028	0.035
Z		1.42		0.056

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